



# BUK7K17-80E

Dual N-channel 80 V, 17 mΩ standard level MOSFET

17 August 2017

Product data sheet

## 1. General description

Dual Standard level N-channel MOSFET in an LFPK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Dual MOSFET
- AEC-Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with  $V_{GS(th)}$  rating of greater than 1 V at 175 °C

## 3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

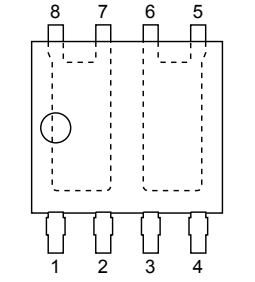
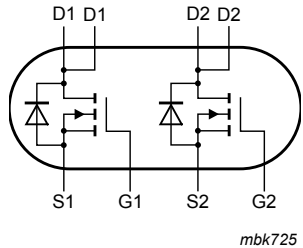
## 4. Quick reference data

Table 1. Quick reference data

| Symbol                                       | Parameter                        | Conditions                                                                                                                                       | Min | Typ  | Max  | Unit |
|----------------------------------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|------|
| <b>Limiting values FET1 and FET2</b>         |                                  |                                                                                                                                                  |     |      |      |      |
| $V_{DS}$                                     | drain-source voltage             | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                                                                       | -   | -    | 80   | V    |
| $I_D$                                        | drain current                    | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                                                        | -   | -    | 21   | A    |
| $P_{tot}$                                    | total power dissipation          | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                                                 | -   | -    | 64   | W    |
| <b>Static characteristics FET1 and FET2</b>  |                                  |                                                                                                                                                  |     |      |      |      |
| $R_{DS(on)}$                                 | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>                                                    | -   | 12.5 | 16.7 | mΩ   |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |                                                                                                                                                  |     |      |      |      |
| $Q_{GD}$                                     | gate-drain charge                | $I_D = 10\text{ A}$ ; $V_{DS} = 64\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> | -   | 10.4 | -    | nC   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                      | Graphic symbol                                                                                |
|-----|--------|-------------|---------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | S1     | source1     | <br>LFPAK56D (SOT1205) | <br>mbk725 |
| 2   | G1     | gate1       |                                                                                                         |                                                                                               |
| 3   | S2     | source2     |                                                                                                         |                                                                                               |
| 4   | G2     | gate2       |                                                                                                         |                                                                                               |
| 5   | D2     | drain2      |                                                                                                         |                                                                                               |
| 6   | D2     | drain2      |                                                                                                         |                                                                                               |
| 7   | D1     | drain1      |                                                                                                         |                                                                                               |
| 8   | D1     | drain1      |                                                                                                         |                                                                                               |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package  |                                                                                                                  |         |
|-------------|----------|------------------------------------------------------------------------------------------------------------------|---------|
|             | Name     | Description                                                                                                      | Version |
| BUK7K17-80E | LFPAK56D | plastic, single ended surface mounted package (LFPAK56D); 8 leads; 1.27 mm pitch; 4.7 mm x 5.3 mm x 1.05 mm body | SOT1205 |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK7K17-80E | 71780E       |

## 8. Limiting values

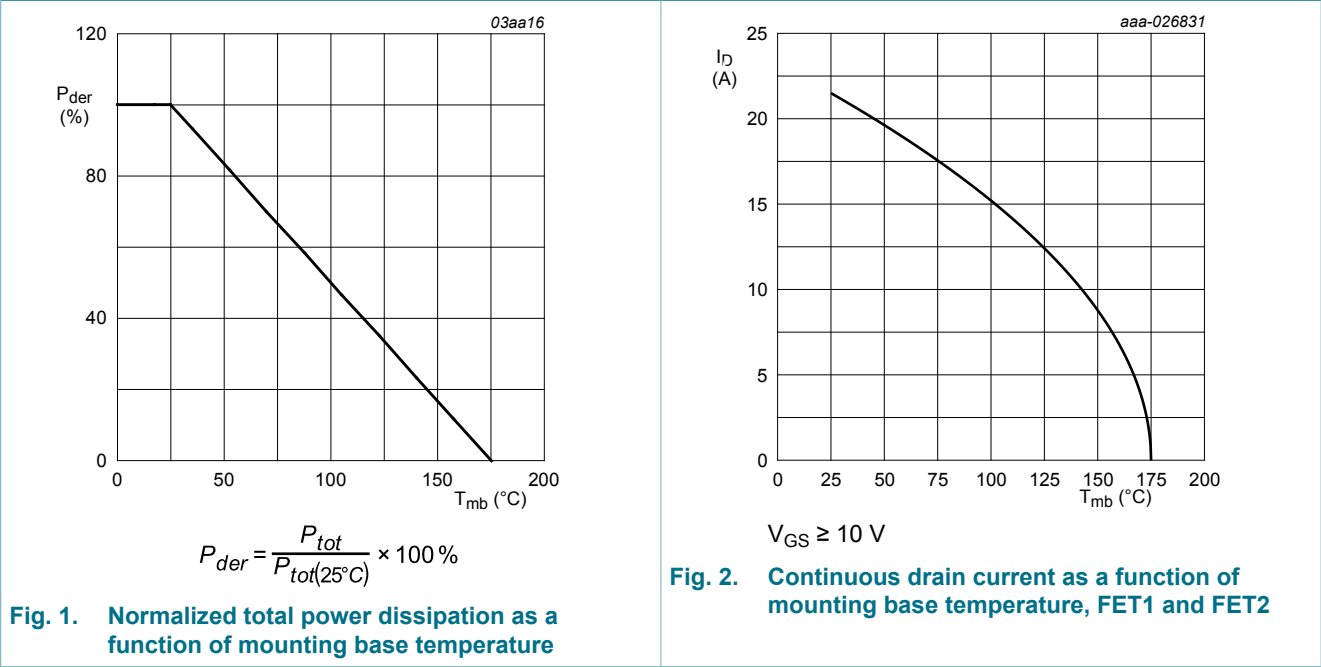
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                               | Parameter               | Conditions                                                                  | Min | Max | Unit |
|--------------------------------------|-------------------------|-----------------------------------------------------------------------------|-----|-----|------|
| <b>Limiting values FET1 and FET2</b> |                         |                                                                             |     |     |      |
| $V_{DS}$                             | drain-source voltage    | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                  | -   | 80  | V    |
| $V_{DGR}$                            | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$                                                | -   | 80  | V    |
| $V_{GS}$                             | gate-source voltage     | DC; $T_j \leq 175\text{ °C}$                                                | -20 | 20  | V    |
| $P_{tot}$                            | total power dissipation | $T_{mb} = 25\text{ °C}$ ; Fig. 1                                            | -   | 64  | W    |
| $I_D$                                | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 2                   | -   | 21  | A    |
|                                      |                         | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 2                  | -   | 15  | A    |
| $I_{DM}$                             | peak drain current      | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 3 | -   | 84  | A    |

| Symbol                             | Parameter                                    | Conditions                                                                                                                                      |         | Min | Max | Unit |
|------------------------------------|----------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------|---------|-----|-----|------|
| T <sub>stg</sub>                   | storage temperature                          |                                                                                                                                                 |         | -55 | 175 | °C   |
| T <sub>j</sub>                     | junction temperature                         |                                                                                                                                                 |         | -55 | 175 | °C   |
| Source-drain diode FET1 and FET2   |                                              |                                                                                                                                                 |         |     |     |      |
| I <sub>S</sub>                     | source current                               | T <sub>mb</sub> = 25 °C                                                                                                                         |         | -   | 21  | A    |
| I <sub>SM</sub>                    | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C                                                                                         |         | -   | 84  | A    |
| Avalanche ruggedness FET1 and FET2 |                                              |                                                                                                                                                 |         |     |     |      |
| E <sub>DS(AL)S</sub>               | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 21 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; Fig. 4 | [1] [2] | -   | 116 | mJ   |

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.  
[2] Refer to application note AN10273 for further information.



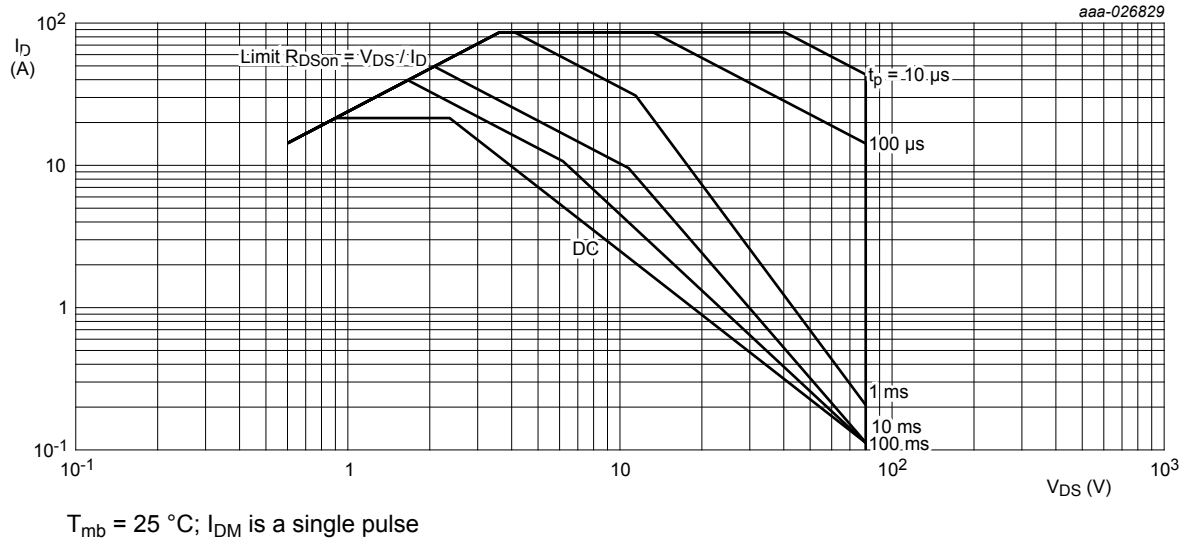


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage, FET1 and FET2

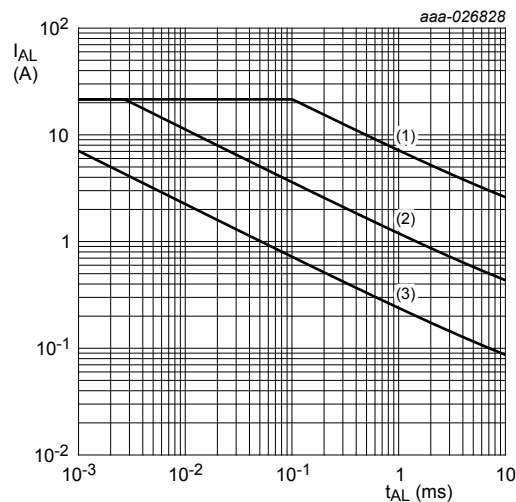
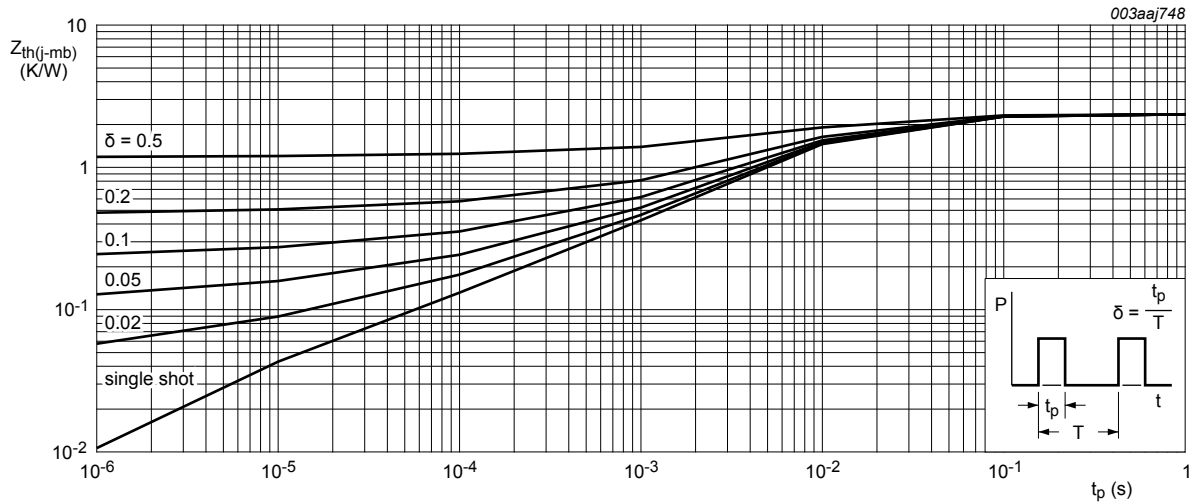


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions                                            | Min | Typ | Max  | Unit |
|----------------|---------------------------------------------------|-------------------------------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5                                                | -   | -   | 2.36 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Minimum footprint; mounted on a printed circuit board | -   | 95  | -    | K/W  |



**Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration, FET1 and FET2**

## 10. Characteristics

**Table 7. Characteristics**

| Symbol                                | Parameter                        | Conditions                                                                                                                                       |  | Min | Typ  | Max  | Unit |
|---------------------------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| Static characteristics FET1 and FET2  |                                  |                                                                                                                                                  |  |     |      |      |      |
| V <sub>(BR)DSS</sub>                  | drain-source breakdown voltage   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                           |  | 80  | -    | -    | V    |
|                                       |                                  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                                                                          |  | 72  | -    | -    | V    |
| V <sub>GS(th)</sub>                   | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>               |  | 2.4 | 3    | 4    | V    |
|                                       |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <a href="#">Fig. 10</a>                                       |  | -   | -    | 4.5  | V    |
|                                       |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <a href="#">Fig. 10</a>                                       |  | 1   | -    | -    | V    |
| I <sub>DSS</sub>                      | drain leakage current            | V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                            |  | -   | 0.02 | 1    | μA   |
|                                       |                                  | V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                                                                           |  | -   | -    | 500  | μA   |
| I <sub>GSS</sub>                      | gate leakage current             | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                            |  | -   | 2    | 100  | nA   |
|                                       |                                  | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                           |  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>                     | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>                                                   |  | -   | 12.5 | 16.7 | mΩ   |
|                                       |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 12</a>                                                  |  | -   | -    | 42   | mΩ   |
| Dynamic characteristics FET1 and FET2 |                                  |                                                                                                                                                  |  |     |      |      |      |
| Q <sub>G(tot)</sub>                   | total gate charge                | I <sub>D</sub> = 10 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |  | -   | 32.4 | -    | nC   |
| Q <sub>GS</sub>                       | gate-source charge               |                                                                                                                                                  |  | -   | 7.1  | -    | nC   |
| Q <sub>GD</sub>                       | gate-drain charge                |                                                                                                                                                  |  | -   | 10.4 | -    | nC   |
| C <sub>iss</sub>                      | input capacitance                | V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>                                        |  | -   | 1701 | 2262 | pF   |
| C <sub>oss</sub>                      | output capacitance               |                                                                                                                                                  |  | -   | 174  | 208  | pF   |

| Symbol                           | Parameter                    | Conditions                                                                                                                       |  | Min | Typ  | Max | Unit |
|----------------------------------|------------------------------|----------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|------|
| C <sub>rss</sub>                 | reverse transfer capacitance |                                                                                                                                  |  | -   | 104  | 142 | pF   |
| t <sub>d(on)</sub>               | turn-on delay time           | V <sub>DS</sub> = 60 V; R <sub>L</sub> = 5 Ω; V <sub>GS</sub> = 10 V;<br>R <sub>G(ext)</sub> = 5 Ω; T <sub>J</sub> = 25 °C       |  | -   | 8.1  | -   | ns   |
| t <sub>r</sub>                   | rise time                    |                                                                                                                                  |  | -   | 11.1 | -   | ns   |
| t <sub>d(off)</sub>              | turn-off delay time          |                                                                                                                                  |  | -   | 22.5 | -   | ns   |
| t <sub>f</sub>                   | fall time                    |                                                                                                                                  |  | -   | 13.4 | -   | ns   |
| Source-drain diode FET1 and FET2 |                              |                                                                                                                                  |  |     |      |     |      |
| V <sub>SD</sub>                  | source-drain voltage         | I <sub>S</sub> = 10 A; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C; Fig. 16                                                    |  | -   | 0.8  | 1.2 | V    |
| t <sub>rr</sub>                  | reverse recovery time        | I <sub>S</sub> = 10 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V;<br>V <sub>DS</sub> = 25 V; T <sub>J</sub> = 25 °C |  | -   | 30.1 | -   | ns   |
| Q <sub>r</sub>                   | recovered charge             |                                                                                                                                  |  | -   | 37.1 | -   | nC   |

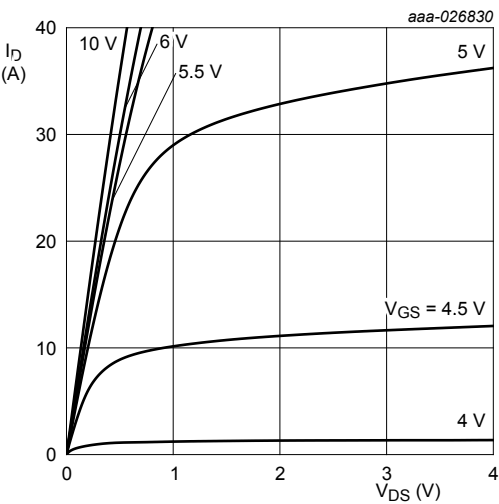


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values, FET1 and FET2

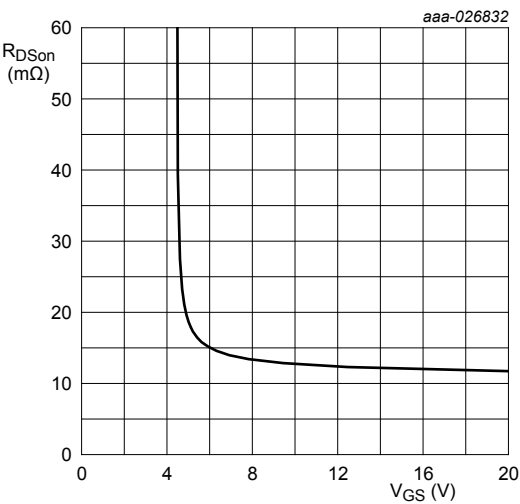


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1 and FET2

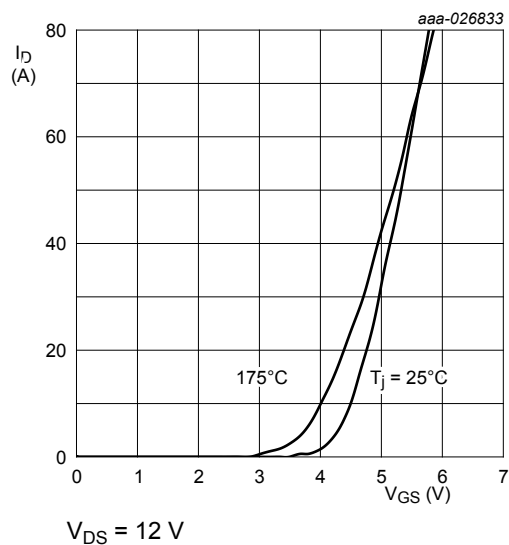


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values, FET1 and FET2

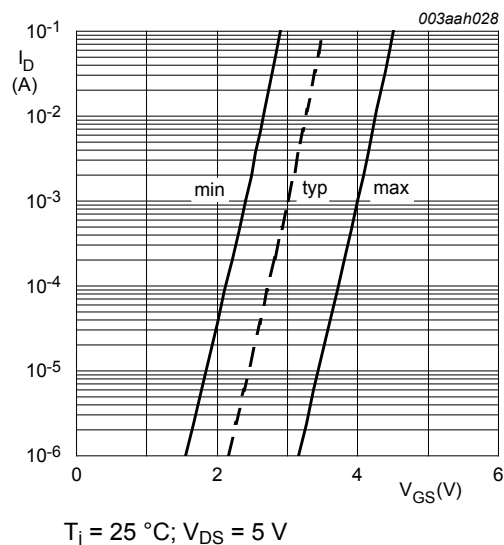


Fig. 9. Sub-threshold drain current as a function of gate-source voltage, FET1 and FET2

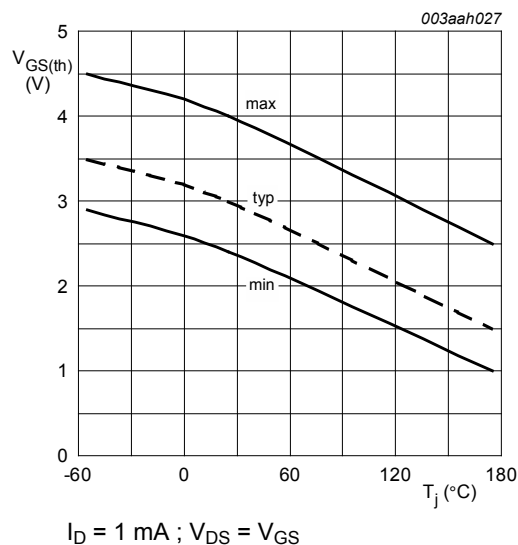


Fig. 10. Gate-source threshold voltage as a function of junction temperature, FET1 and FET2

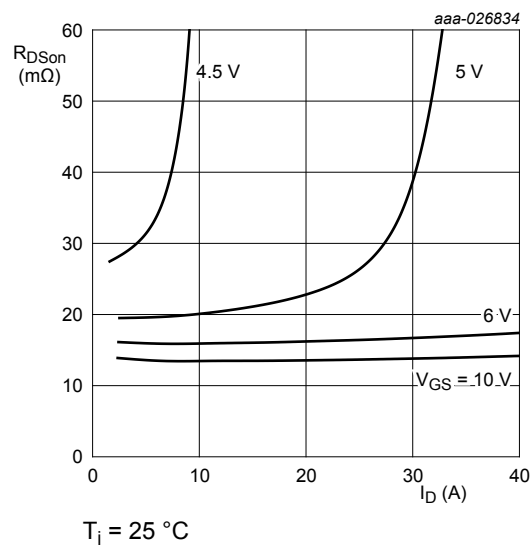
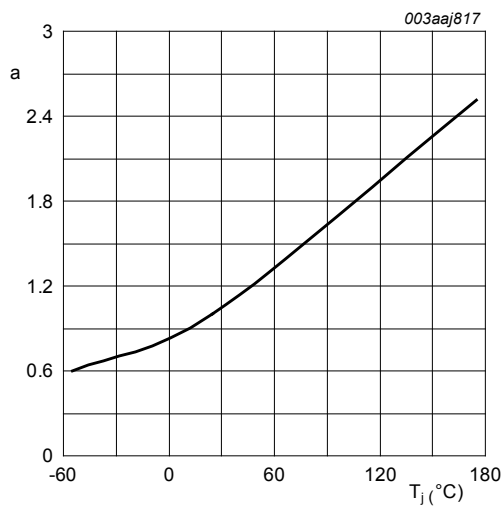
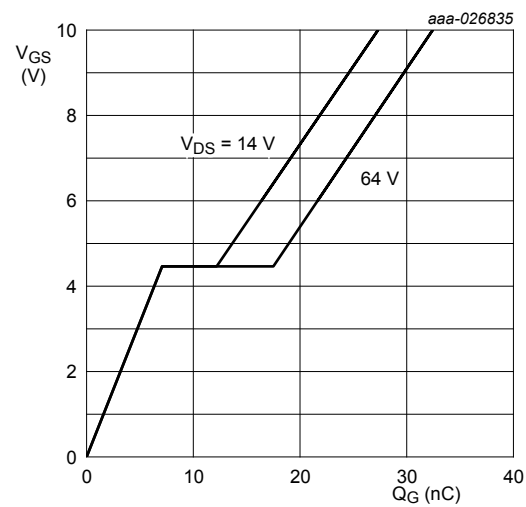


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values, FET1 and FET2



$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature, FET1 and FET2



$T_j = 25^{\circ}\text{C}$ ;  $I_D = 10$  A

Fig. 13. Gate-source voltage as a function of gate charge; typical values, FET1 and FET2

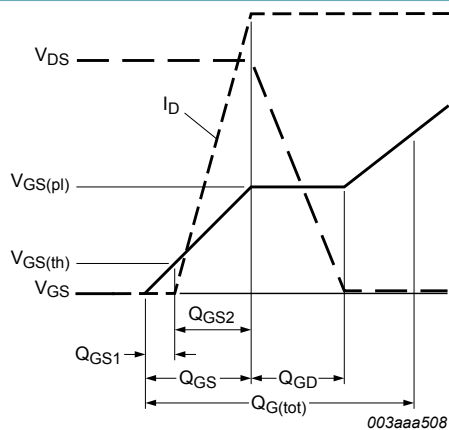
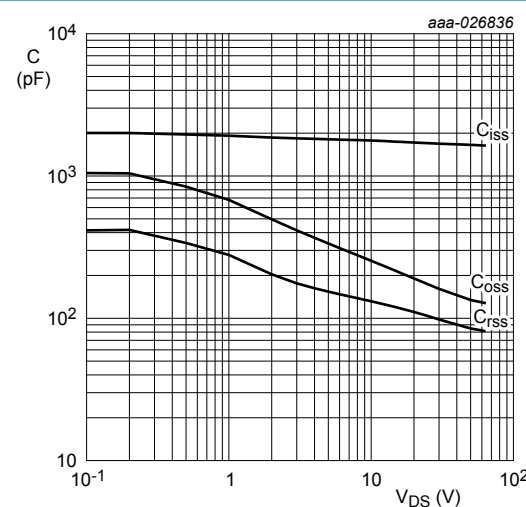


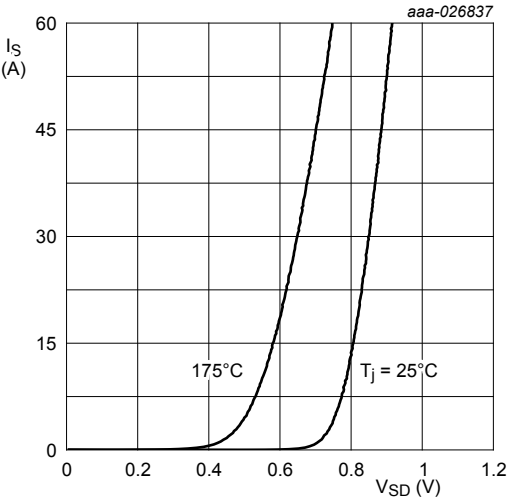
Fig. 14. Gate charge waveform definitions



$V_{GS} = 0$  V;  $f = 1$  MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values, FET1 and FET2





$V_{GS} = 0\text{ V}$

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values, FET1 and FET2

11. Package outline

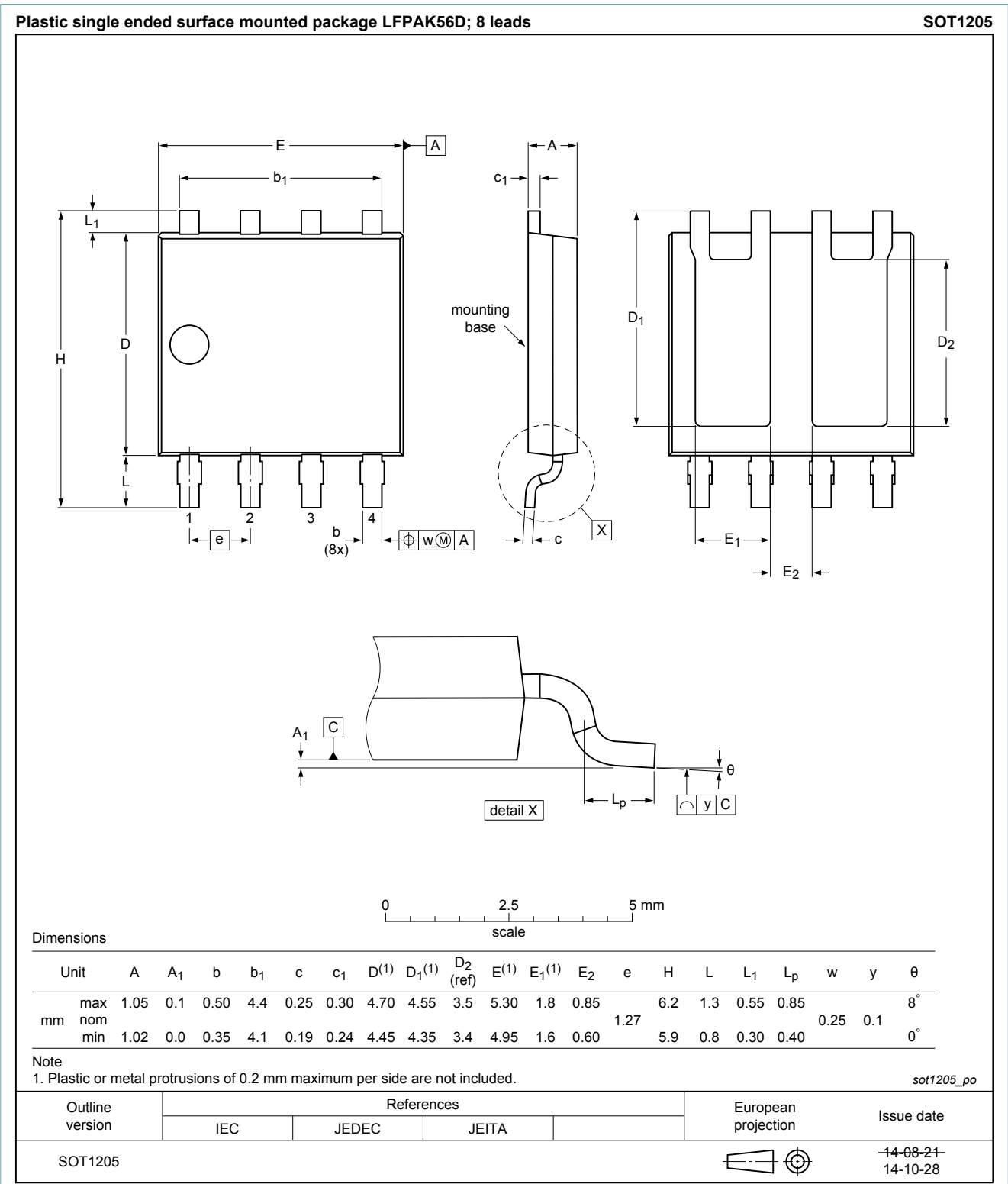


Fig. 17. Package outline LPAK56D (SOT1205)

## 12. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
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